

# Polyimide Resist SX AR-PC 5000/80.2

## Thermally stable resist, also applicable as protective coating

Experimental sample/custom-made product

#### Characterisation

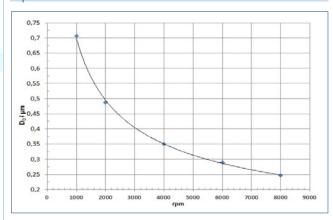
- not light-sensitive > 300 nm, no yellow light required
- thin protective film for surface protection
- plasma etching resistant, thermally stable up to 450 °C
- applicable as sensor material or insulating layer
- structurable in two-component system with  $\ensuremath{\mathsf{AR-P}}$  3500 T
- polyimide
- safer solvent PGMEA and N-methyl pyrrolidone

#### Properties I

Parameter / AR-PC	5000/80.2
Solids content (%)	10
Viscosity 25°C (mPas)	19
Film thickness/4000 rpm (µm)	0.4
Resolution (µm)	-
Contrast	-
Flash point (°C)	52
Storage temperature (°C)*	8 - 12

<sup>\*</sup> Products have a guaranteed shelf life of temperatures from the date of sale if stored correctly and can also be used without guarantee until the date indicated on the label.

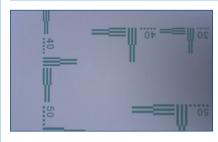
#### Spin curve



#### Properties II

Glass transition temperature °C	17	0
Dielectric constant	2.	9
Cauchy-Koeffizienten	$N_0$	1.581
	$N_1$	146.7
	$N_2$	0
Plasma etching rates (nm/min)	Ar-sputtering	5
(5 Pa. 240-250 V Bias)	$O_2$	208
	CF <sub>4</sub>	43
	80 CF <sub>4</sub>	186
	+ 16 O <sub>2</sub>	

#### Resist structures



Resist structures of AR-PC 5000/80.2 After processing in two-component system with AR-P 3510 T

#### Structural formula

#### Process parameters

Substrat	Si 4" wafer	
Soft bake	150 °C, 2 min, hot plate	

#### Process chemicals

Adhesion promoter	AR 300-80 new
Developer	1-layer system: - 2-layer system: AR 300-46
Thinner	X AR 300-12/3
Remover	AR 300-76, 300-47

## Polyimide Resist SX AR-PC 5000/80.2

### Process conditions - One-layer process

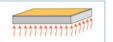
This diagram shows exemplary process steps for resist SX AR-PC 5000/80.2. All specifications are guideline values which have to be adapted to own specific conditions.

Pre-coating with AR 300-80



Adhesive bonding at 2000 rpm, resulting film thickness 15 nm

1. Soft bake



180 °C, 2 min hot plate or

180 °C, 25 min convection oven

Coating protective film with SX AR-PC 5000/80.2



1000 rpm, 60 s, 0.8 μm

2. Soft bake (± 1 °C)



100 °C, 2 min hot plate or

95 °C, 30 min convection oven

Removal AR-PC 5000/80.2 (optional)



AR 300-76 or O<sub>2</sub> plasma ashing

#### Processing instructions

If SX AR-PC 5000/80.2 is only required as protective coating, as sensor material or for insulation purposes, the process is finished after the 2nd tempering step.



# Polyimid Photoresist SX AR-PC 5000/80.2

### Process conditions - Two-layer process

Dieses Schema zeigt ein Prozessierungsbeispiel für den Resist SX AR-PC 5000/80.2. Die Angaben sind Richtwerte, die auf die eigenen spezifischen Bedingungen angepasst werden müssen.

Pre-coating with AR 300-80		Adhesive bonding at 2000 rpm, resulting film thickness 15 nm
1. Soft bake	11111111111111111111111111111111111111	180 °C, 2 min hot plate or 180 °C, 25 min convection oven
Coating protective film with SX AR-PC 5000/80.2		1000 rpm, 60 s, 0.8 μm
2. Soft bake (± 1 °C)	,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	100 °C, 2 min hot plate or 95 °C °C, 30 min convection oven
Coating AR-P 3540 T		4000 rpm, 1.4 μm
3. Soft bake (± 1 °C)	mmmmm	100 °C, 2 min hot plate or 95 °C, 30 min convection oven
UV exposure		Broadband UV, 365 nm, 405 nm, 436 nm Exposure dose (E <sub>0</sub> , BB-UV stepper): 120 mJ/cm <sup>2</sup> , 1,4 µm
Development of both resist film (21-23 °C $\pm$ 0.5 °C) puddle	ns	AR 300-46, 40 s
Rinse		DI-H <sub>2</sub> O, 30 s
Flood exposure		Broadband UV, 240 mJ/cm <sup>2</sup>
Removal AR-P 3540 T		AR 300-47, 20 s Only polyimide structures remain
Removal AR-P 5000/80.2		AR 300-76 or O <sub>2</sub> plasma ashing

#### Processing instructions

(optional)

For a two-component structuring however, an additional coating with photoresist is necessary. The two-component system can be developed in one step after exposure.

Developer AR 300-46 begins to dissolve exposed areas of AR-P 3540 T as usual and then attacks the underlying polyimide in anisotropic manner, i.e. the structures in polyimide widen only marginally. A prolonged exposure (> 1.5 min) however results in a pronounced undercut.